

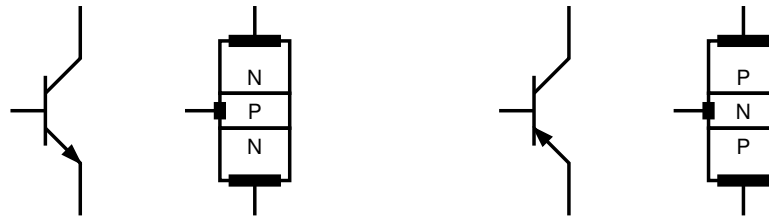
Overview of Technologies

Components for Logic

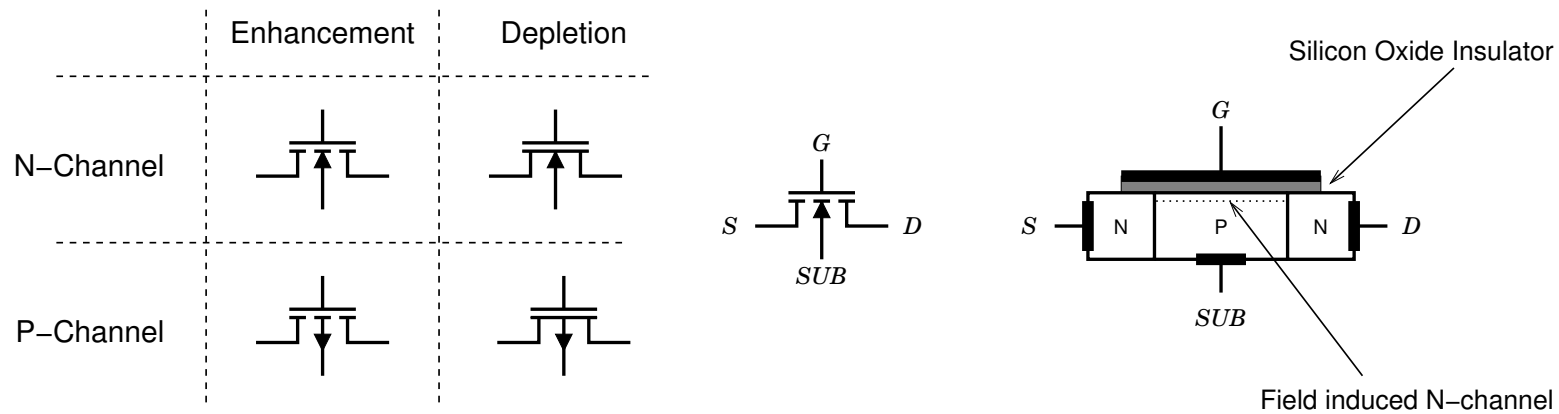
Diode



Bipolar Transistors

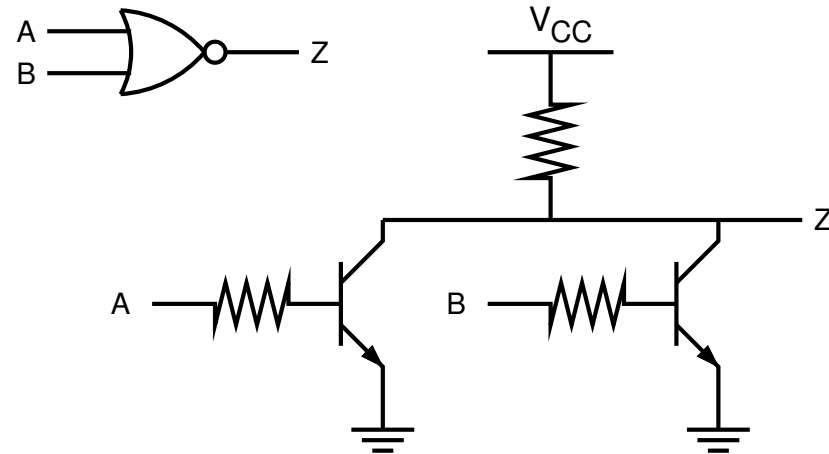
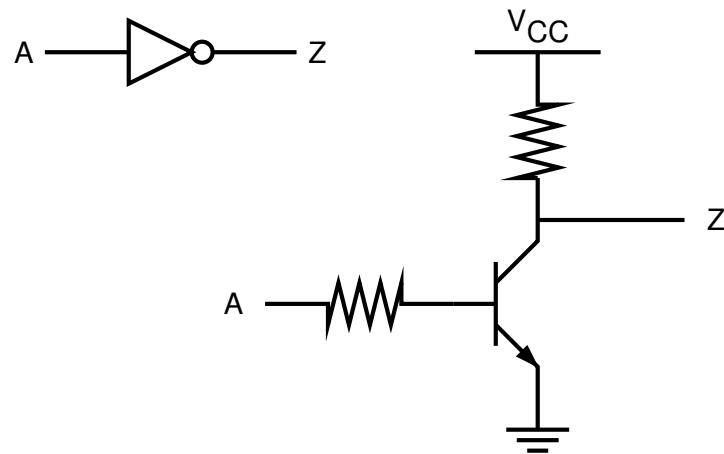


MOS Transistors



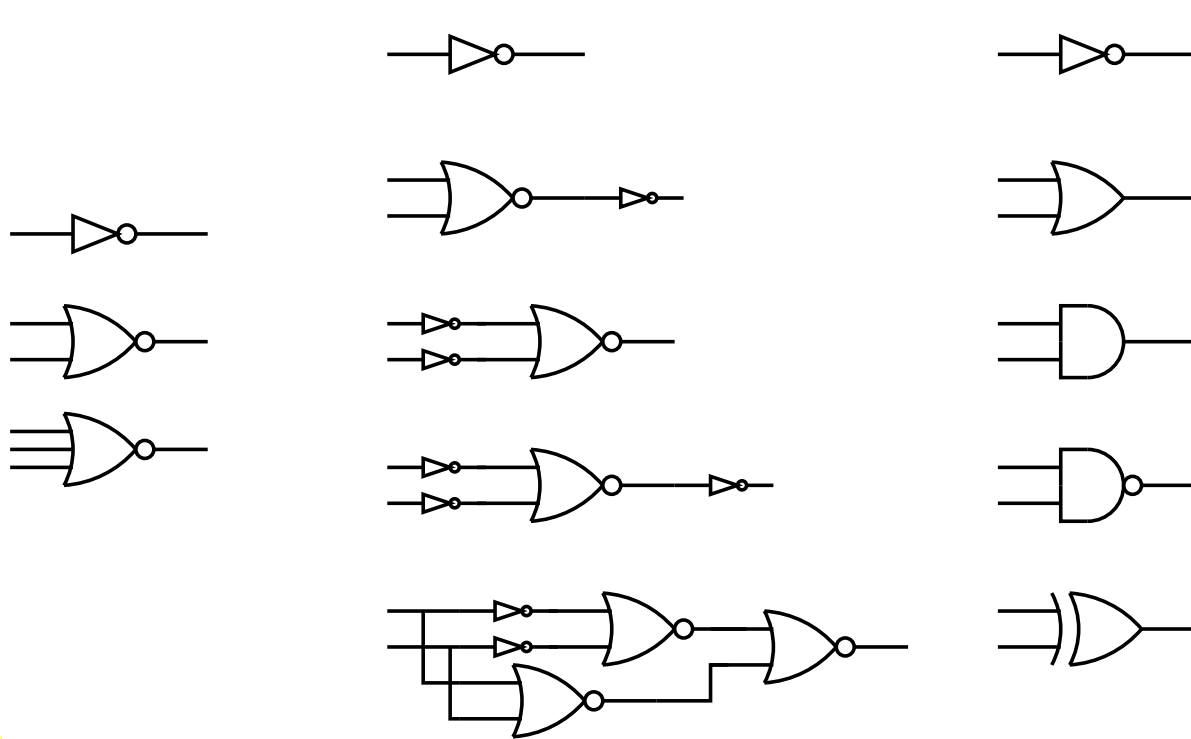
Overview of Technologies

RTL Inverter and NOR gate



Overview of Technologies

All functions can be realized using only the NOR gates¹ available in the RTL logic family.²

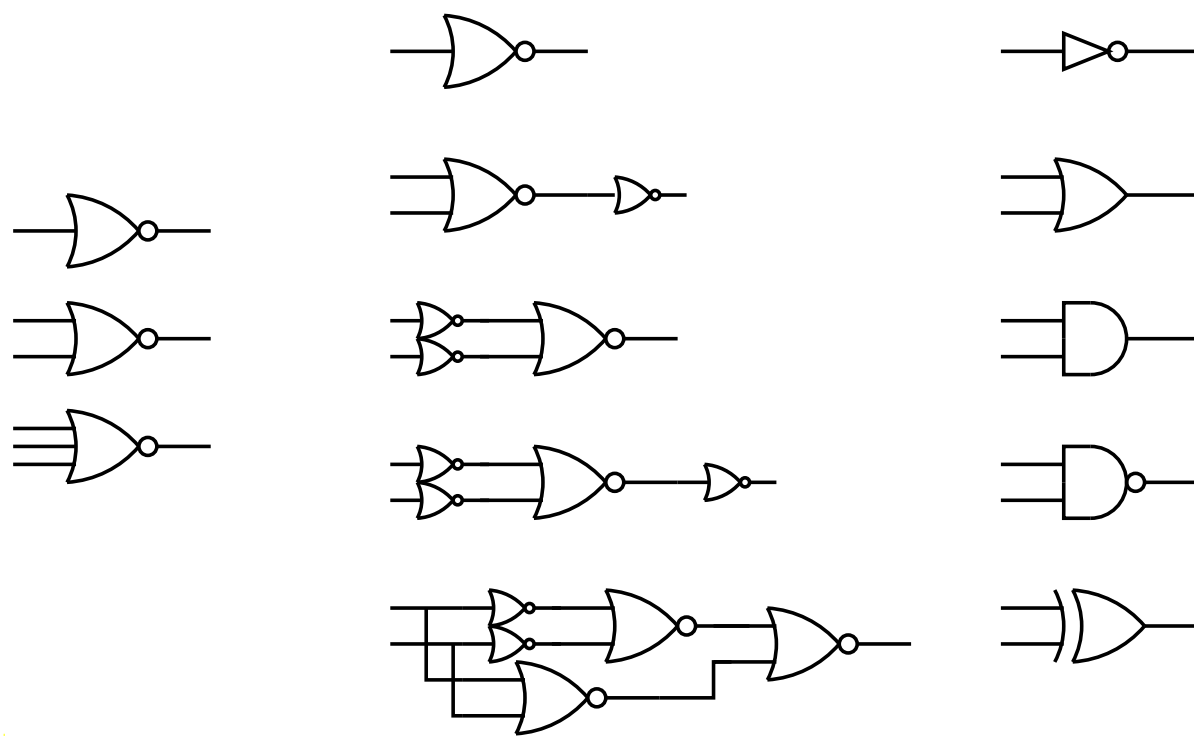


1

2

Overview of Technologies

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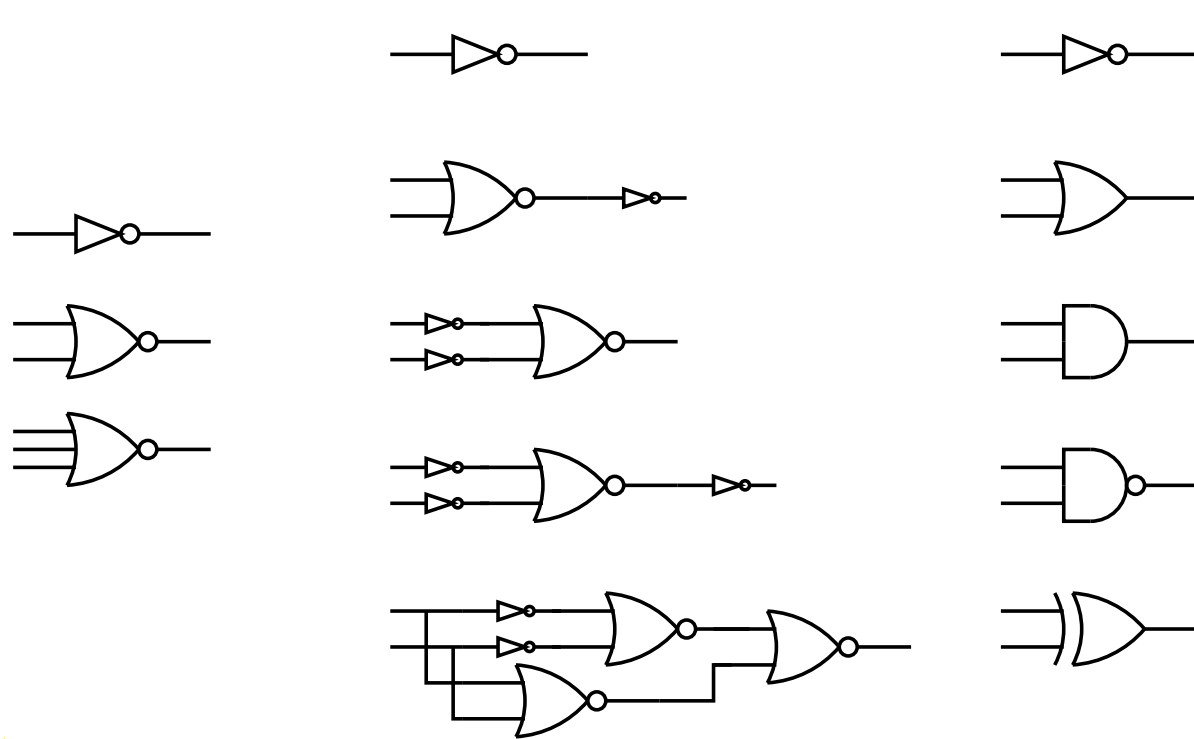


¹Note that an inverter is a special case of a NOR gate with only one input.

²

Overview of Technologies

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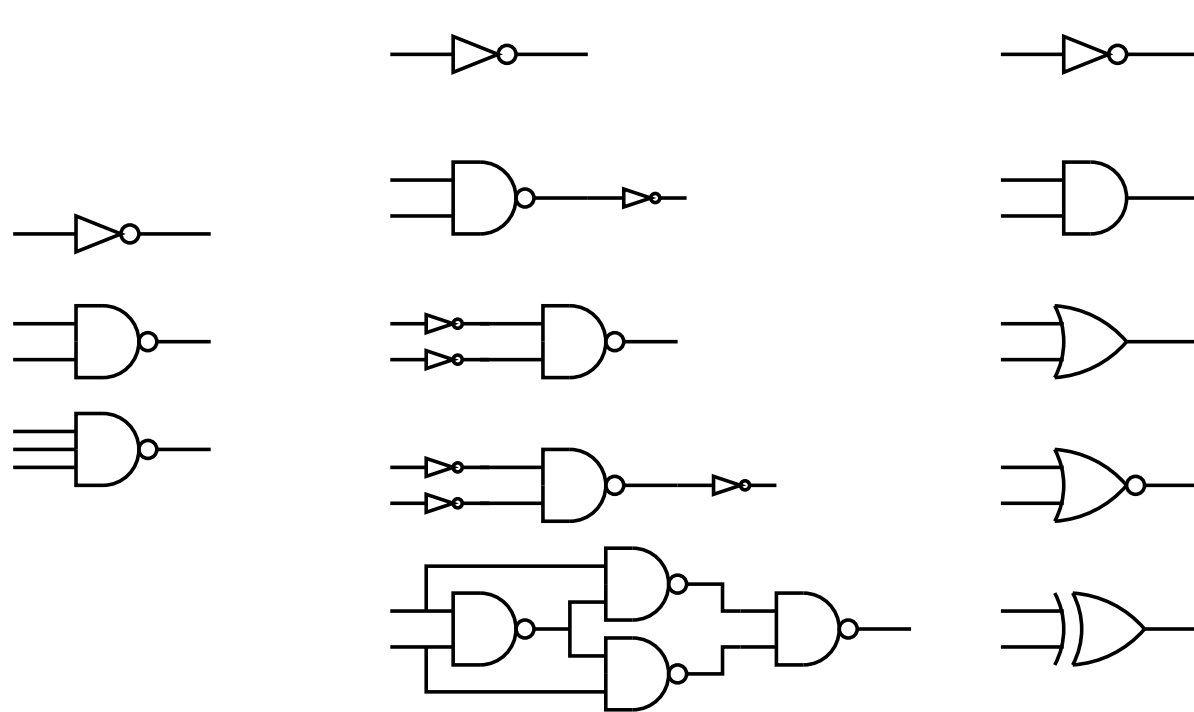


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Overview of Technologies

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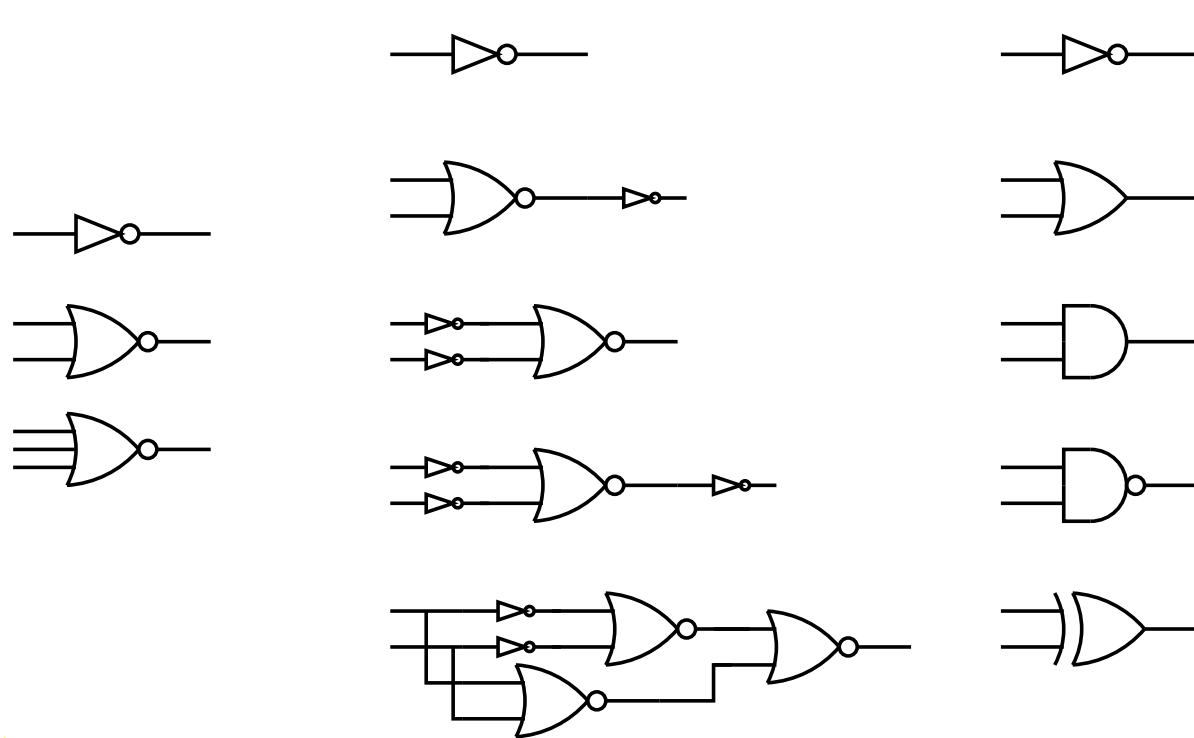


¹Note that an inverter is a special case of a NAND gate with only one input.

²NAND gates could be used instead for logic families which support only NAND gates.

Overview of Technologies

All functions can be realized using only the NOR gates¹ available in the RTL logic family.²



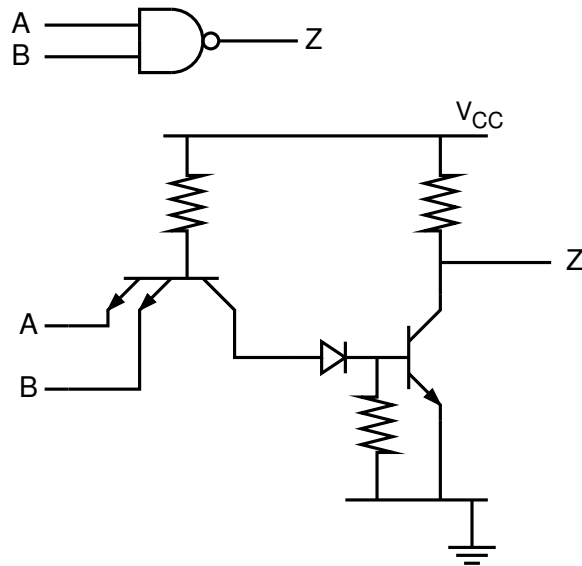
¹Note that an inverter is a special case of a NOR gate with only one input.

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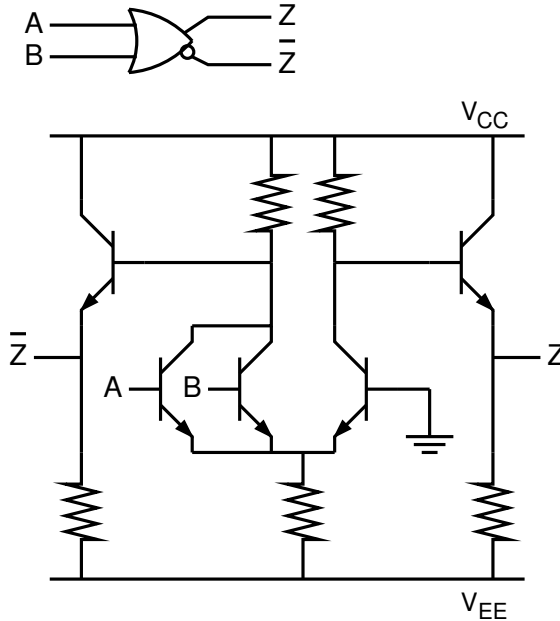
Overview of Technologies

Other Bipolar Technologies

TTL NAND Gate



ECL OR/NOR Gate

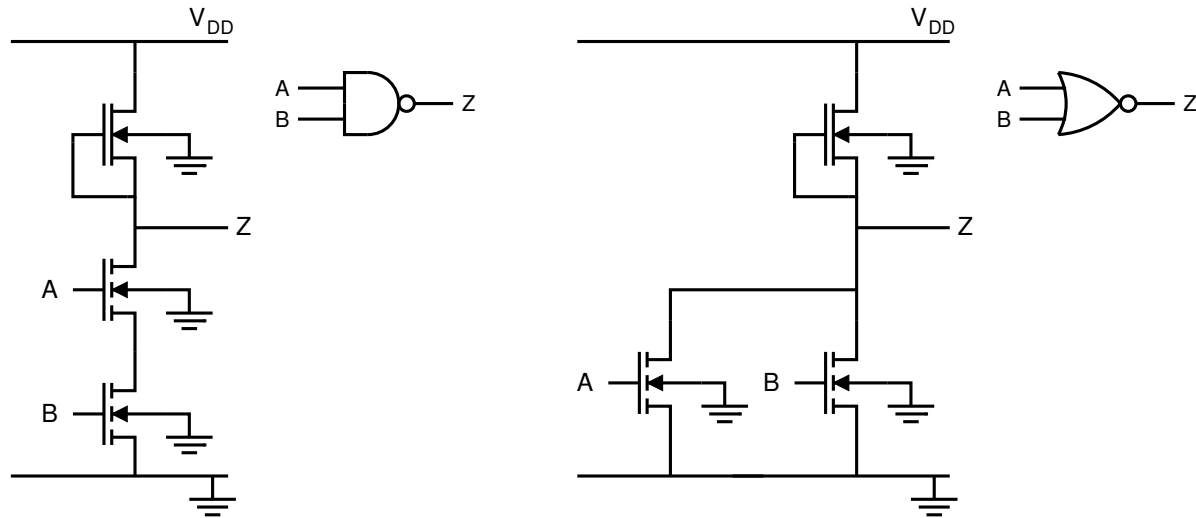


- TTL gives faster switching than RTL at the expense of greater complexity³. The characteristic multi-emitter transistor reduces the overall component count.
- ECL is a very high speed, high power, non-saturating technology.

³Most TTL families are more complex than the basic version shown here

Overview of Technologies

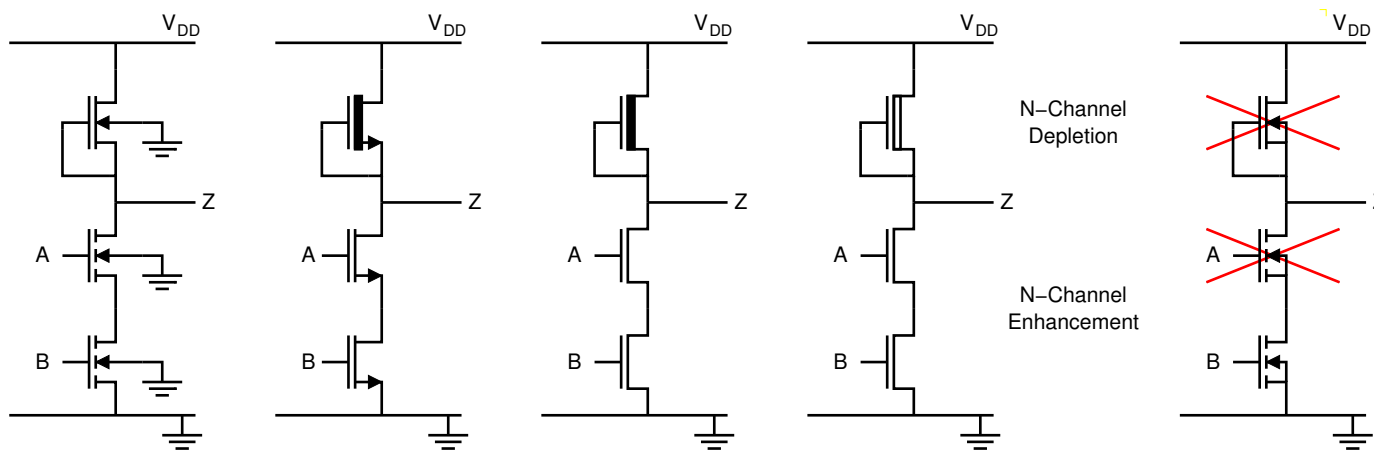
NMOS - a VLSI technology.



- Circuit function determined by series/parallel combination of devices.
- Depletion transistor acts as non-linear load resistor.
Resistance increases as the enhancement device turns on, thus reducing power consumption.
- The low output voltage is determined by the size ratio of the devices.

Overview of Technologies

Alternative transistors representations for NMOS circuits



Various shorthands are used for simplifying NMOS circuit diagrams.

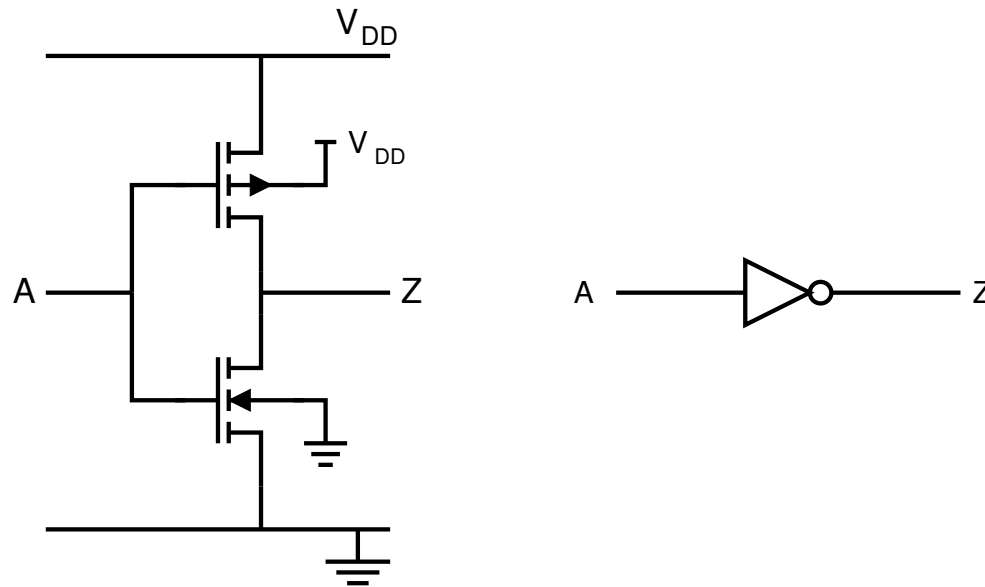
- Substrate connections need not be drawn since all must connect to Gnd.
- Since source and drain are indistinguishable in the layout, there is no need to show the source on the circuit diagram.

Note that schematic tools not designed for IC design will usually include inappropriate 3-terminal symbols.

Overview of Technologies

CMOS logic

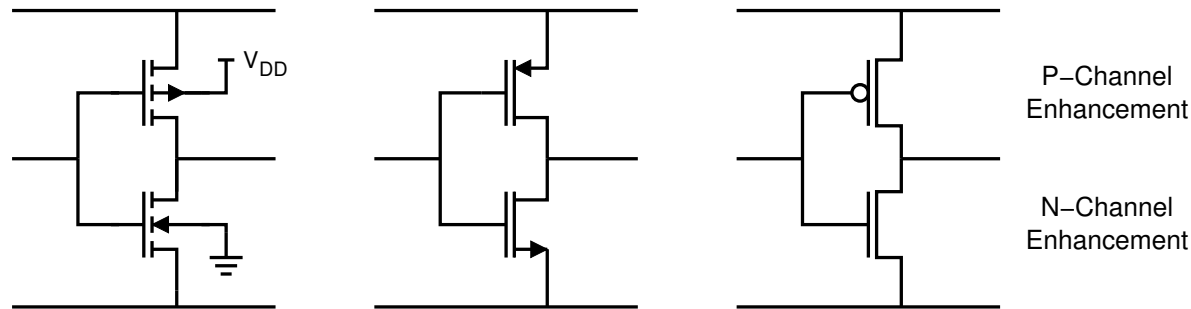
CMOS - *state of the art* VLSI.



- An active PMOS device complements the NMOS device giving:
 - rail to rail output swing.
 - negligible static power consumption.

Digital CMOS Circuits

Alternative transistor representations for CMOS circuits



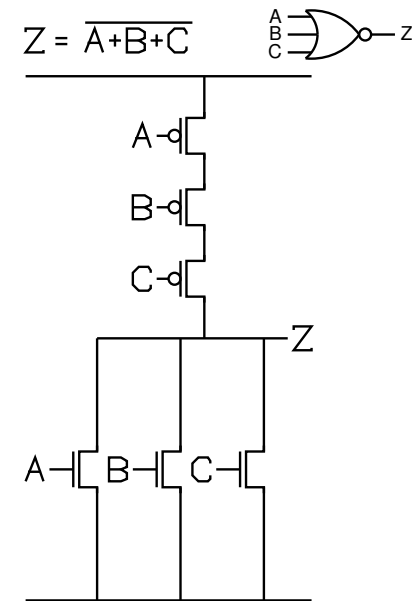
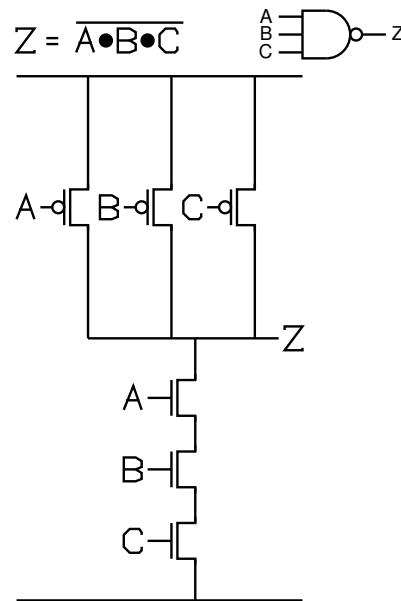
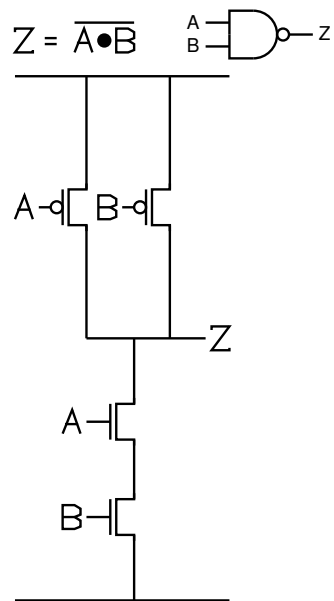
Digital CMOS circuits⁴ tend to use simplified symbols like their NMOS counterparts.

- In general substrate connections are not drawn where they connect to V_{DD} (PMOS) and Gnd (NMOS).
- All CMOS devices are enhancement mode.
- Transistors act as simple digitally controlled switches.

⁴in analog CMOS circuits we may have wells not connected to V_{DD} /GND

Digital CMOS Circuits

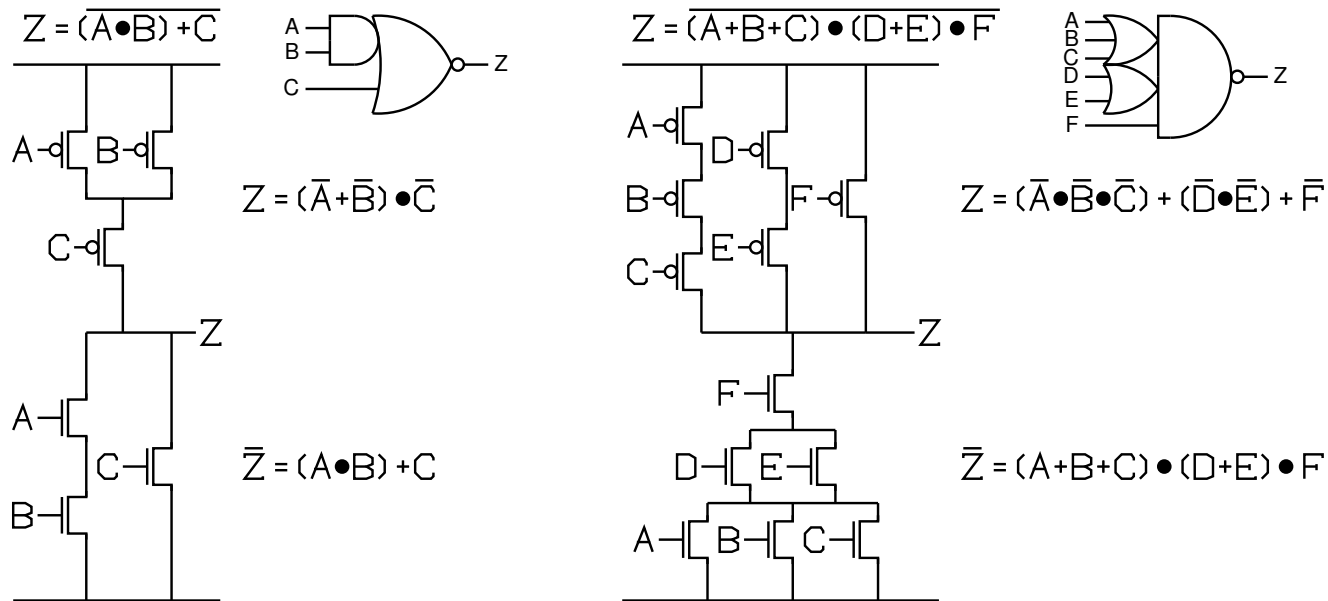
Static CMOS complementary gates



- For any set of inputs there will exist either a path to Vdd or a path to Gnd.

Digital CMOS Circuits

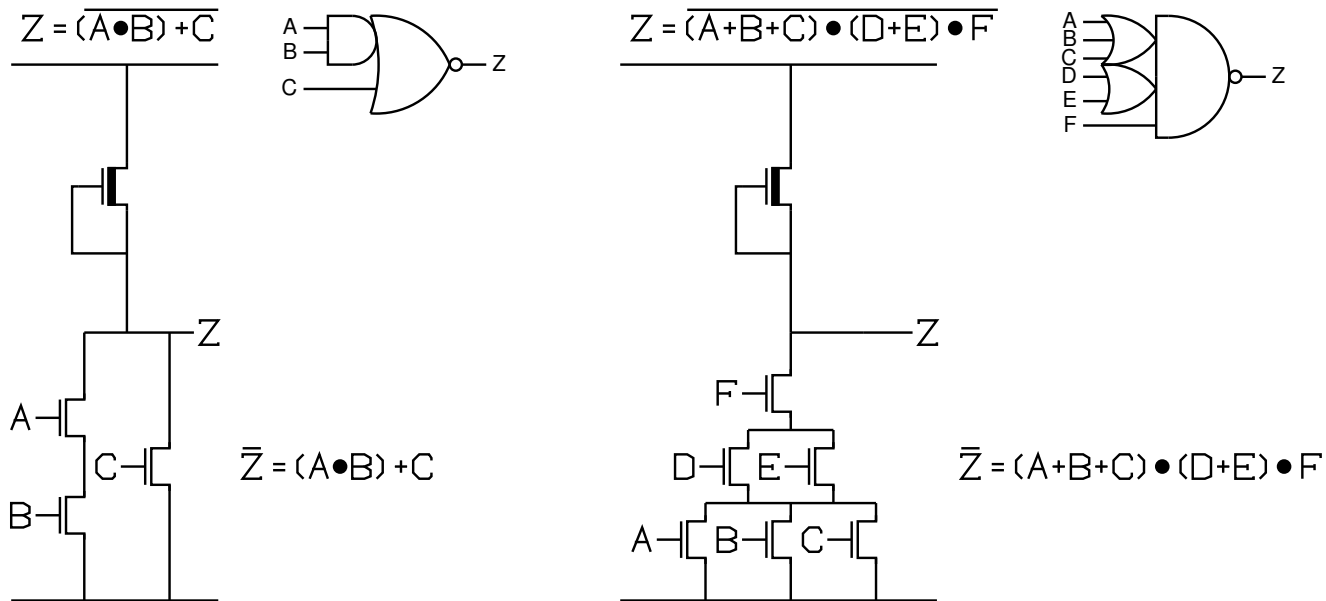
Compound Gates



- All compound gates are inverting.
- Realisable functions are arbitrary AND/OR expressions with inverted output.

Digital NMOS Circuits

Compound Gates



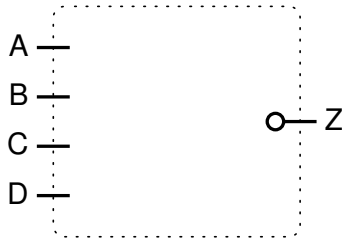
- All compound gates are inverting.
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Digital CMOS Circuits

Compound Gate Example

$$Z = \overline{(A \bullet B) + (C \bullet D)}$$

Symbol



Pull Up Network

$$Z = f(\bar{A}, \bar{B}, \bar{C}, \bar{D})$$

$$Z = \dots\dots\dots$$

Pull Down Network

$$\bar{Z} = f(A, B, C, D)$$

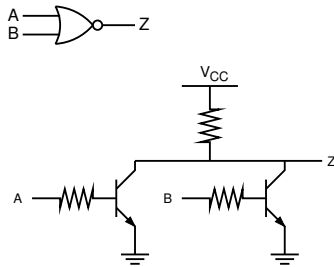
$$\bar{Z} = (A \bullet B) + (C \bullet D)$$

————— V_{DD}

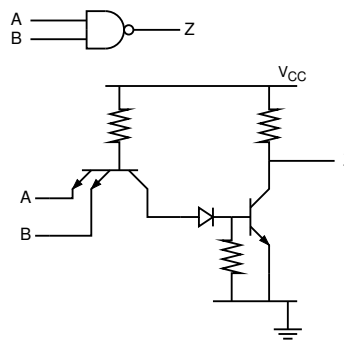
————— Z

————— GND

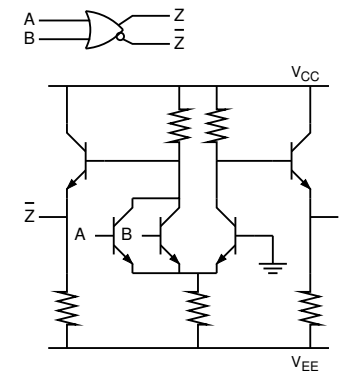
RTL NOR Gate



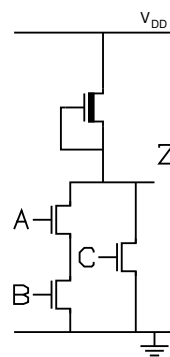
TTL NAND Gate



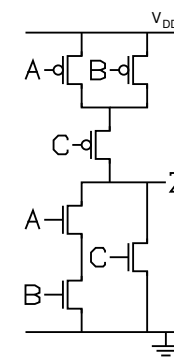
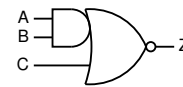
ECL OR/NOR Gate



NMOS Compound Gate



CMOS Compound Gate



- Bipolar Transistors with Resistors - MSI/LSI

RTL - NOR

TTL - NAND

ECL - OR/NOR

- MOS Transistors (no resistors) - VLSI

NMOS

CMOS - No static power!

Both allow construction of NOR, NAND & Compound gate (always inverting)